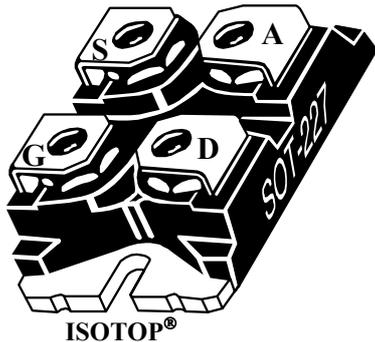
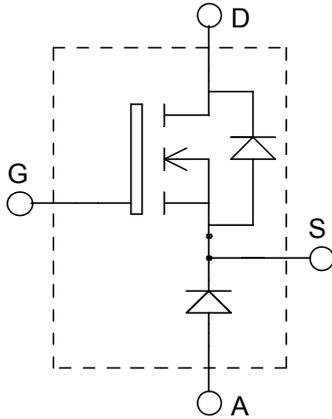


**ISOTOP<sup>®</sup> Buck chopper  
MOSFET Power Module**

$V_{DSS} = 500V$   
 $R_{DSon} = 100m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 41A \text{ @ } T_c = 25^\circ C$


**Application**

- AC and DC motor control
- Switched Mode Power Supplies

**Features**

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very rugged
- Low profile
- RoHS Compliant

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	500	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	41
		$T_c = 80^\circ C$	30
$I_{DM}$	Pulsed Drain current	164	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	100	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	378
$I_{AR}$	Avalanche current (repetitive and non repetitive)	41	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1600	
$I_{F_{AV}}$	Maximum Average Forward Current	Duty cycle=0.5	A
$I_{F_{RMS}}$	RMS Forward Current (Square wave, 50% duty)	$T_c = 80^\circ C$	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 500V			100	μA
		T <sub>j</sub> = 25°C				
R <sub>DS(on)</sub>	Drain – Source on Resistance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 400V			500	mΩ
		T <sub>j</sub> = 125°C				
R <sub>DS(on)</sub>	Drain – Source on Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 23A			100	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 2.5mA	3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0V			±100	nA

**Dynamic Characteristics**

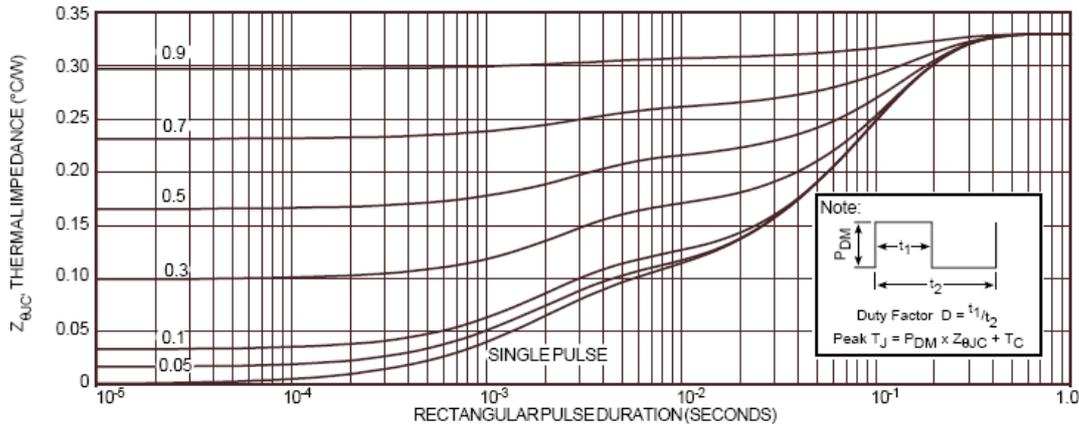
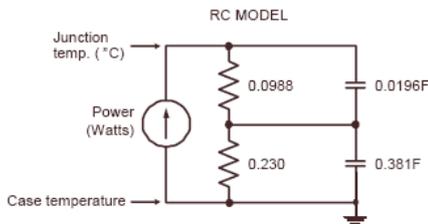
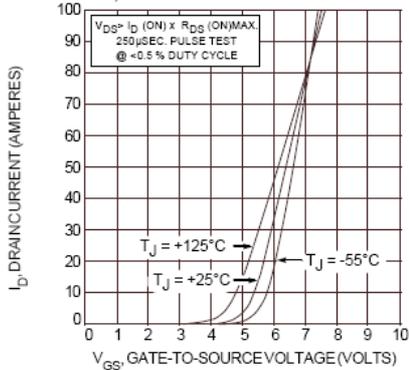
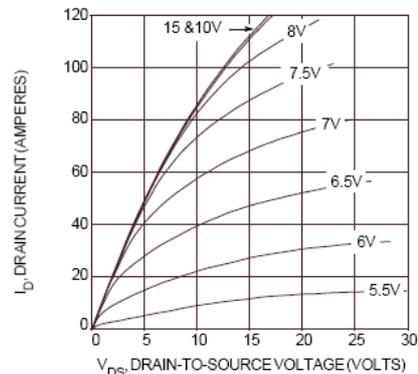
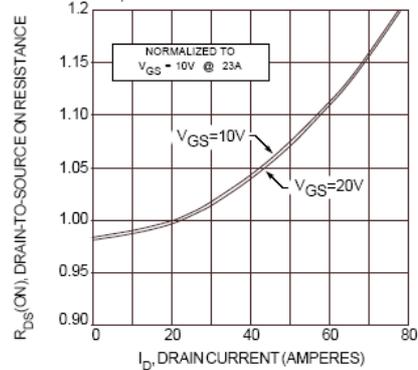
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		4360		pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V		894		
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz		60		
Q <sub>g</sub>	Total gate Charge	V <sub>GS</sub> = 10V		96		nC
Q <sub>gs</sub>	Gate – Source Charge	V <sub>Bus</sub> = 250V		24		
Q <sub>gd</sub>	Gate – Drain Charge	I <sub>D</sub> = 41A @ T <sub>j</sub> = 25°C		49		
T <sub>d(on)</sub>	Turn-on Delay Time	<b>Resistive switching @ 25°C</b>		11		ns
T <sub>r</sub>	Rise Time	V <sub>GS</sub> = 15V		15		
T <sub>d(off)</sub>	Turn-off Delay Time	V <sub>Bus</sub> = 250V		25		
T <sub>f</sub>	Fall Time	I <sub>D</sub> = 41A @ T <sub>j</sub> = 25°C		3		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive Switching @ 25°C</b>		543		μJ
E <sub>off</sub>	Turn-off Switching Energy	V <sub>bus</sub> = 330V, V <sub>GS</sub> = 15V		509		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive Switching @ 125°C</b>		843		μJ
E <sub>off</sub>	Turn-off Switching Energy	V <sub>bus</sub> = 330V, V <sub>GS</sub> = 15V		593		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 30A		1.6	1.8	V
		I <sub>F</sub> = 60A		1.9		
		I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C		1.4	
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = 600V	T <sub>j</sub> = 25°C		250	μA
		V <sub>R</sub> = 600V	T <sub>j</sub> = 125°C		500	
C <sub>T</sub>	Junction Capacitance	V <sub>R</sub> = 200V		44		pF
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 1A, V <sub>R</sub> = 30V di/dt = 100A/μs	T <sub>j</sub> = 25°C		23	ns
			T <sub>j</sub> = 25°C		85	
			T <sub>j</sub> = 125°C		160	
I <sub>RRM</sub>	Maximum Reverse Recovery Current	I <sub>F</sub> = 30A V <sub>R</sub> = 400V di/dt = 200A/μs	T <sub>j</sub> = 25°C		4	A
			T <sub>j</sub> = 125°C		8	
			T <sub>j</sub> = 25°C		130	
Q <sub>rr</sub>	Reverse Recovery Charge		T <sub>j</sub> = 25°C		700	nC
			T <sub>j</sub> = 125°C			
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C		70	ns
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>R</sub> = 400V			1300	nC
I <sub>RRM</sub>	Maximum Reverse Recovery Current	di/dt = 1000A/μs			30	A

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	MOSFET		0.33	°C/W
		Diode		1.21	
R <sub>thJA</sub>	Junction to Ambient (IGBT & Diode)			20	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	2500			V
T <sub>J</sub> , T <sub>STG</sub>	Storage Temperature Range	-55		150	°C
T <sub>L</sub>	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**Typical MOSFET Performance Curve**

**FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION**

**FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL**

**FIGURE 4, TRANSFER CHARACTERISTICS**

**FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS**

**FIGURE 5, R\_DS(ON) vs DRAIN CURRENT**

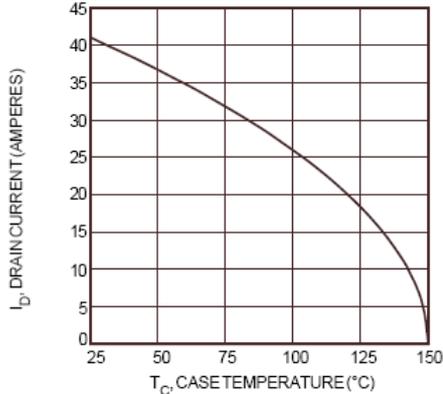


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

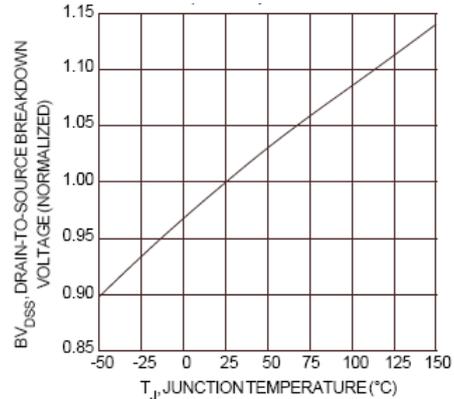


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

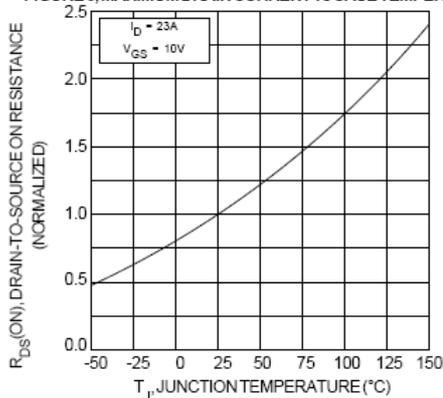


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

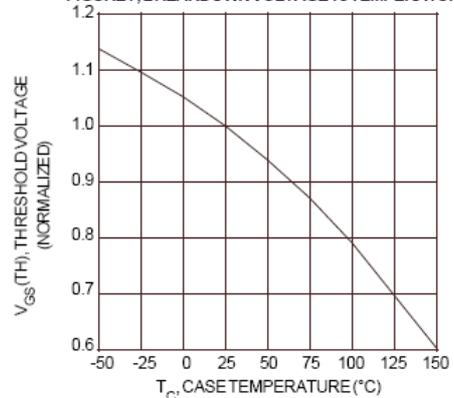


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

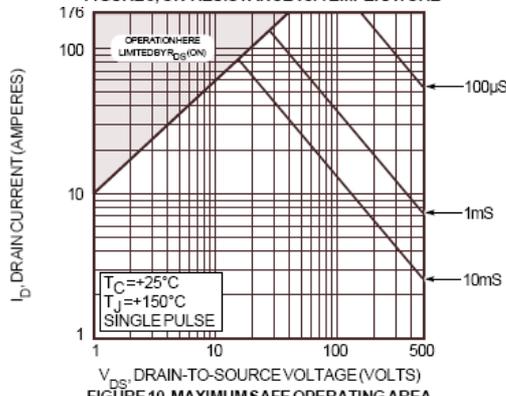


FIGURE 10, MAXIMUM SAFE OPERATING AREA

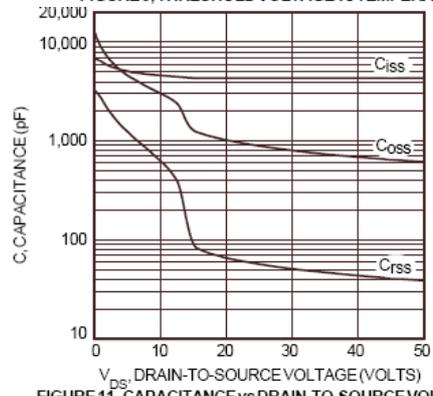


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

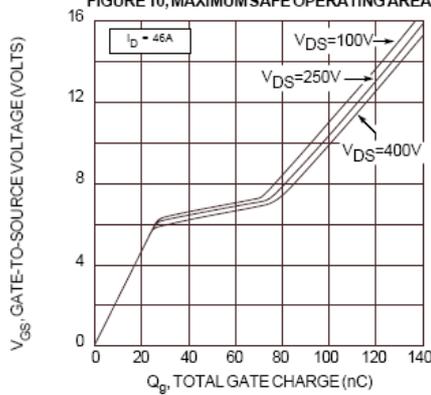


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

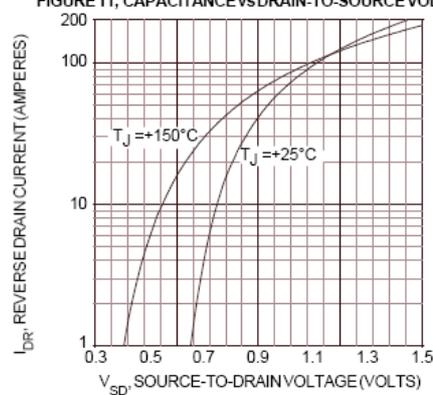


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

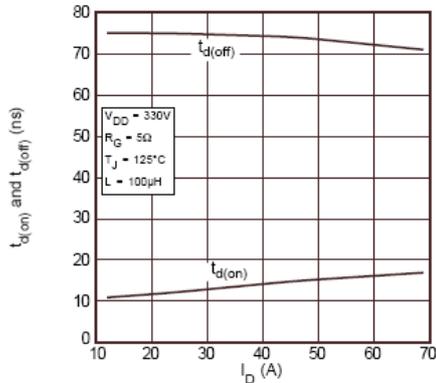


FIGURE 14, DELAY TIMES vs CURRENT

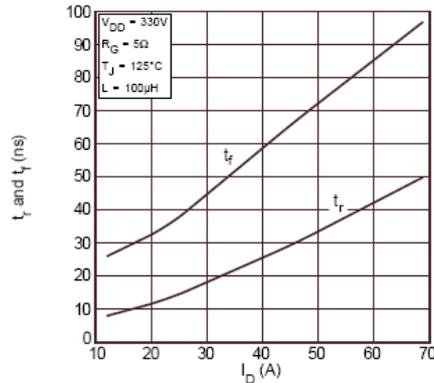


FIGURE 15, RISE AND FALL TIMES vs CURRENT

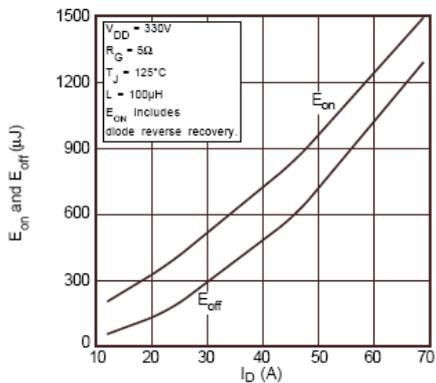


FIGURE 16, SWITCHING ENERGY vs CURRENT

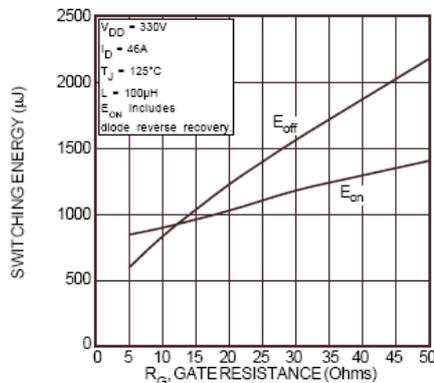


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

### Typical Diode Performance Curve

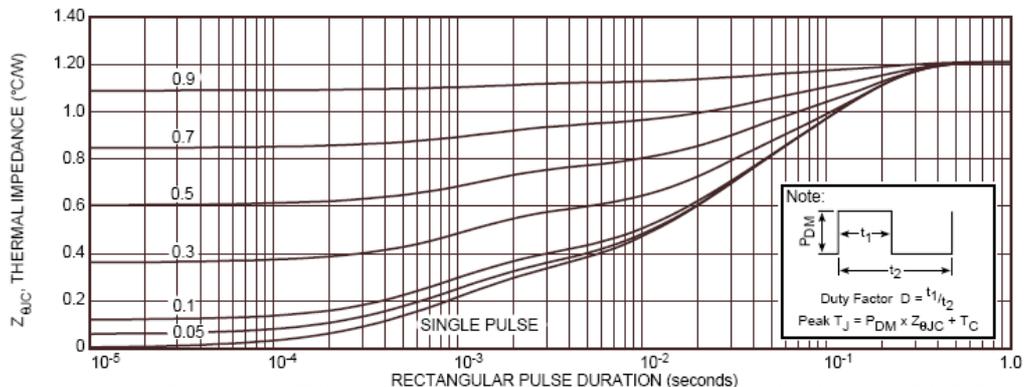


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

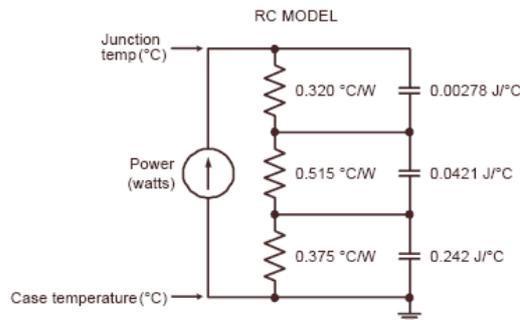


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

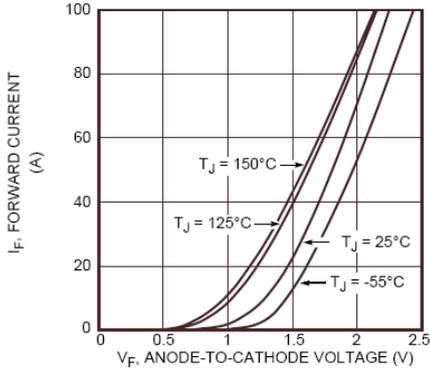


Figure 2. Forward Current vs. Forward Voltage

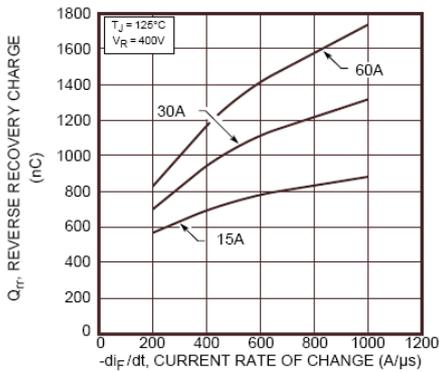


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

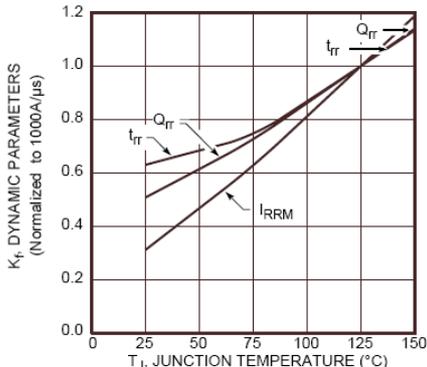


Figure 6. Dynamic Parameters vs. Junction Temperature

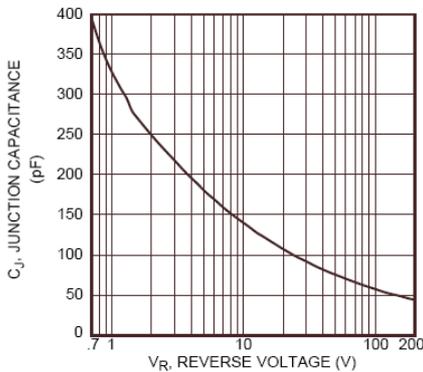


Figure 8. Junction Capacitance vs. Reverse Voltage

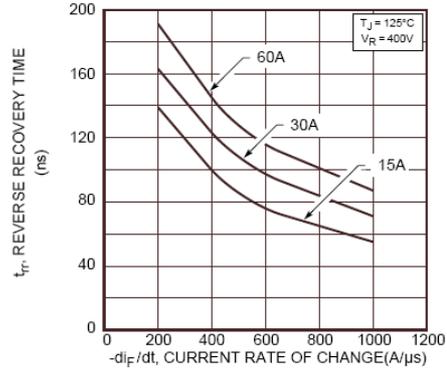


Figure 3. Reverse Recovery Time vs. Current Rate of Change

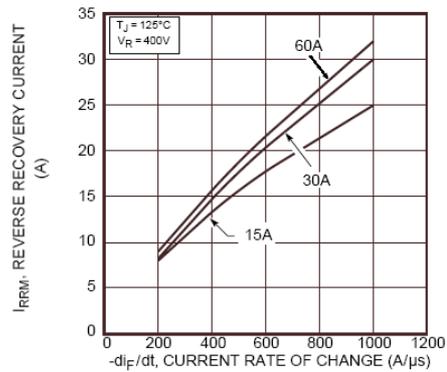


Figure 5. Reverse Recovery Current vs. Current Rate of Change

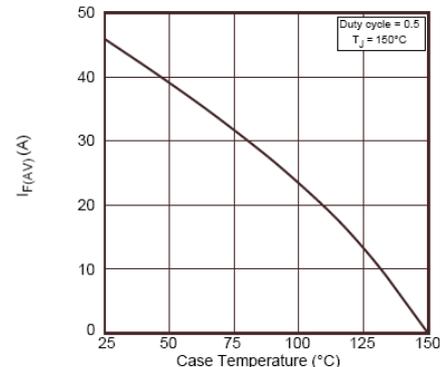


Figure 7. Maximum Average Forward Current vs. Case Temperature

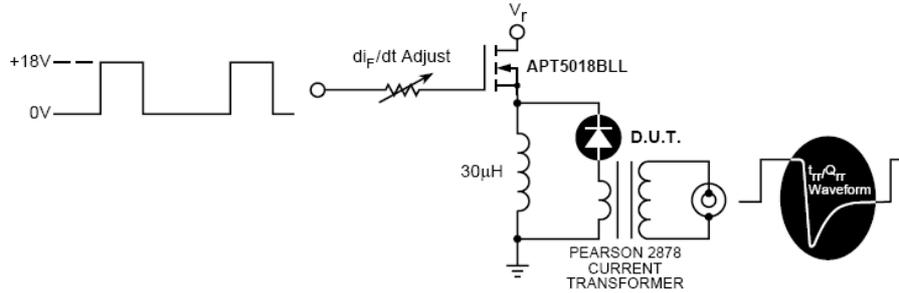


Figure 9. Diode Test Circuit

- ❶  $I_F$  - Forward Conduction Current
- ❷  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- ❸  $I_{RRM}$  - Maximum Reverse Recovery Current.
- ❹  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- ❺  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

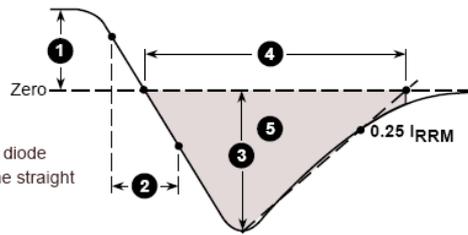
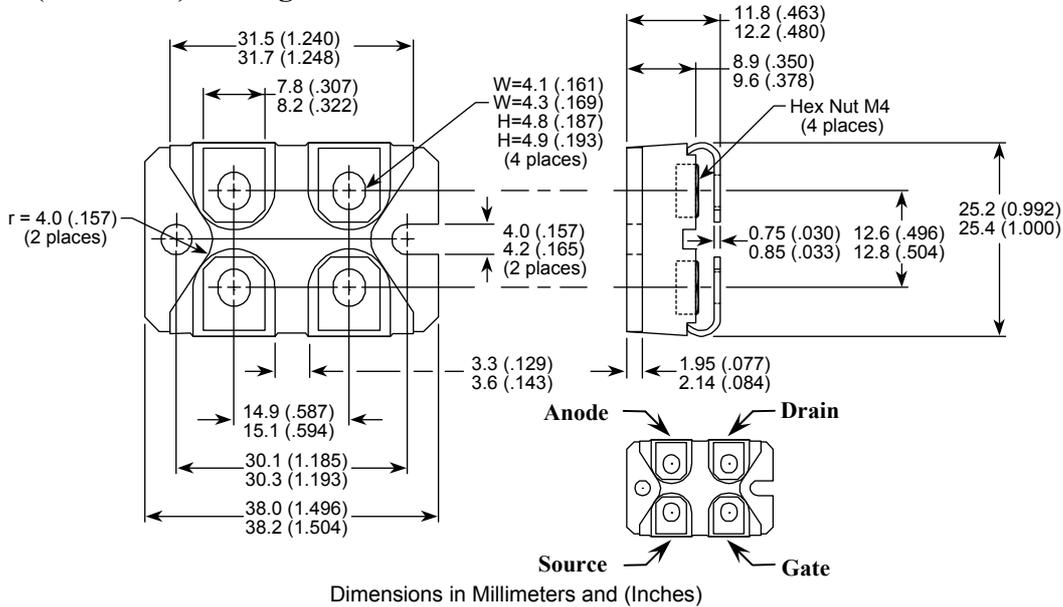


Figure 10. Diode Reverse Recovery Waveform and Definitions

**SOT-227 (ISOTOP<sup>®</sup>) Package Outline**



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